

### Features

- 4-Uni-directional Channels ESD protection
- Typically Used at High Speed Ports
- Low operating voltage: 5V
- Low Channel Input Capacitance of 0.4pF  
Typical for I/Os (Typ)
- -IEC 61000-4-2 (ESD) immunity test  
Air discharge:  $\pm 30\text{kV}$   
Contact discharge:  $\pm 30\text{kV}$
- -IEC61000-4-4 (EFT) 40A (5/50ns)
- Totally Lead-Free & Fully RoHS Compliant
- Halogen and Antimony Free. "Green" Device

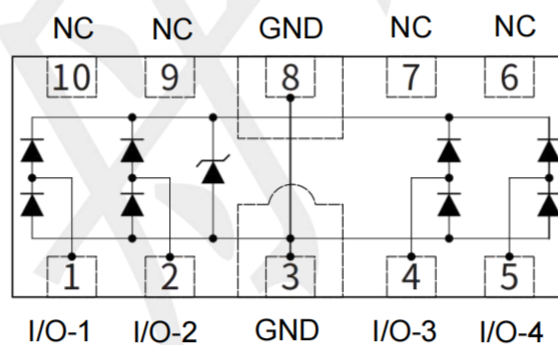
### Mechanical Characteristics

- Package: DFN2510-10
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound
- Terminal Connections: See Diagram Below
- -IEC 61000-4-2 (ESD) immunity test

### Applications

- USB 3.1 & 3.2 and MDDI ports
- PCI express and Serial SATA
- Ports Notebook Computers
- Tablets

### Dimensions and Pin Configuration



**DFN2510-10**

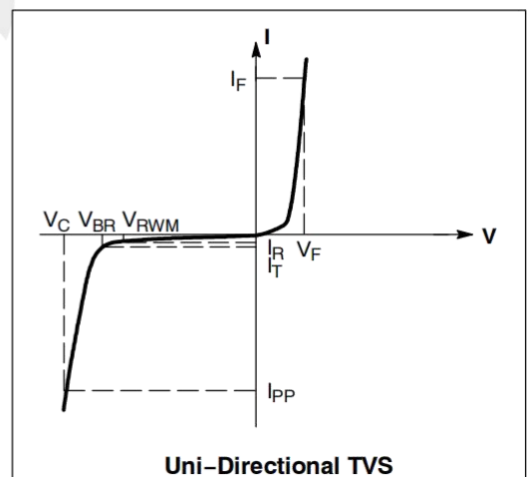
### Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppp	84	W
IEC 61000-4-2 Spec Current at 60 ns (A)	Ipp	8	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±30 ±30	KV
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

### Electrical Characteristics (TA=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM	--	--	5	V	
Breakdown Voltage	VBR	6	--	9.5	V	IT= 1mA
Reverse Leakage Current	IR	--	--	0.1	uA	VRWM=5V
Clamping Voltage	VC	--	5.5	7	V	Ipp=1A(8x 20us pulse)
Clamping Voltage	VC	--	8.5	10.5	V	Ipp=8A(8x 20us pulse)
Junction Capacitance	CJ	--	0.4	0.65	pF	VR = 0V, f = 1MHz, Any I/O pin to GND
Junction Capacitance	CJ	--	0.2	--	pF	VR = 0V, f = 1MHz, Between any I/O pin

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>
P <sub>pk</sub>	Peak Power Dissipation
C	Capacitance @ V <sub>R</sub> = 0 and f = 1.0 MHz



### Characteristic Curves

Fig1. 8/20 $\mu$ s Pulse Waveform

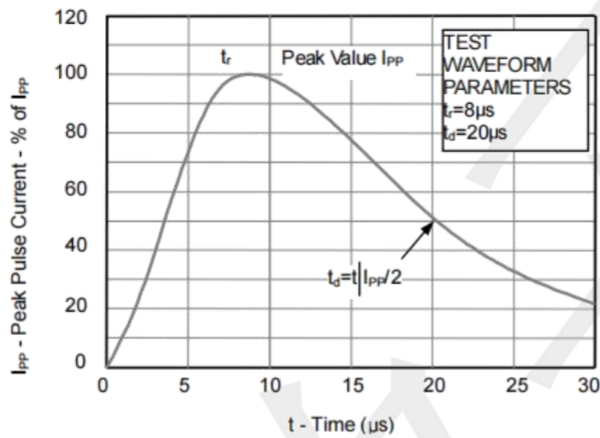


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)

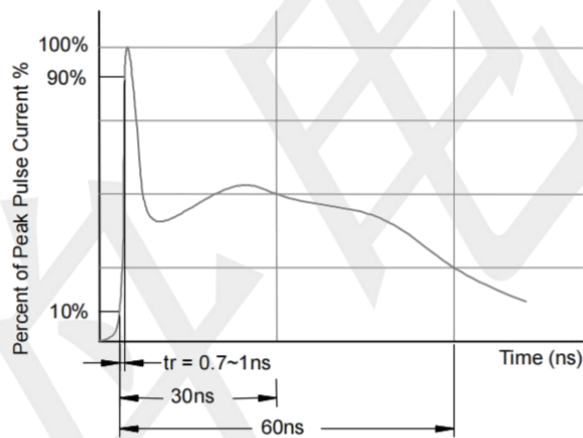
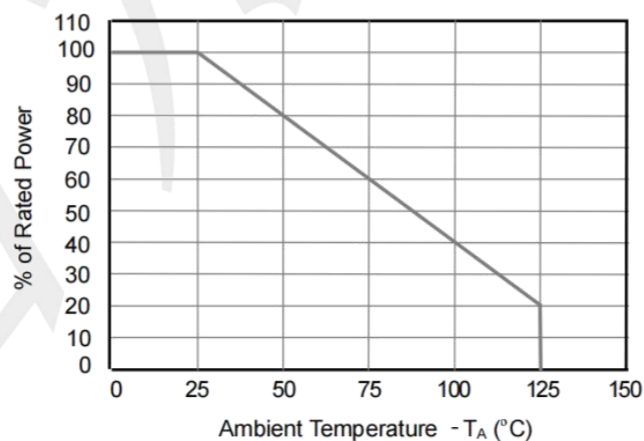
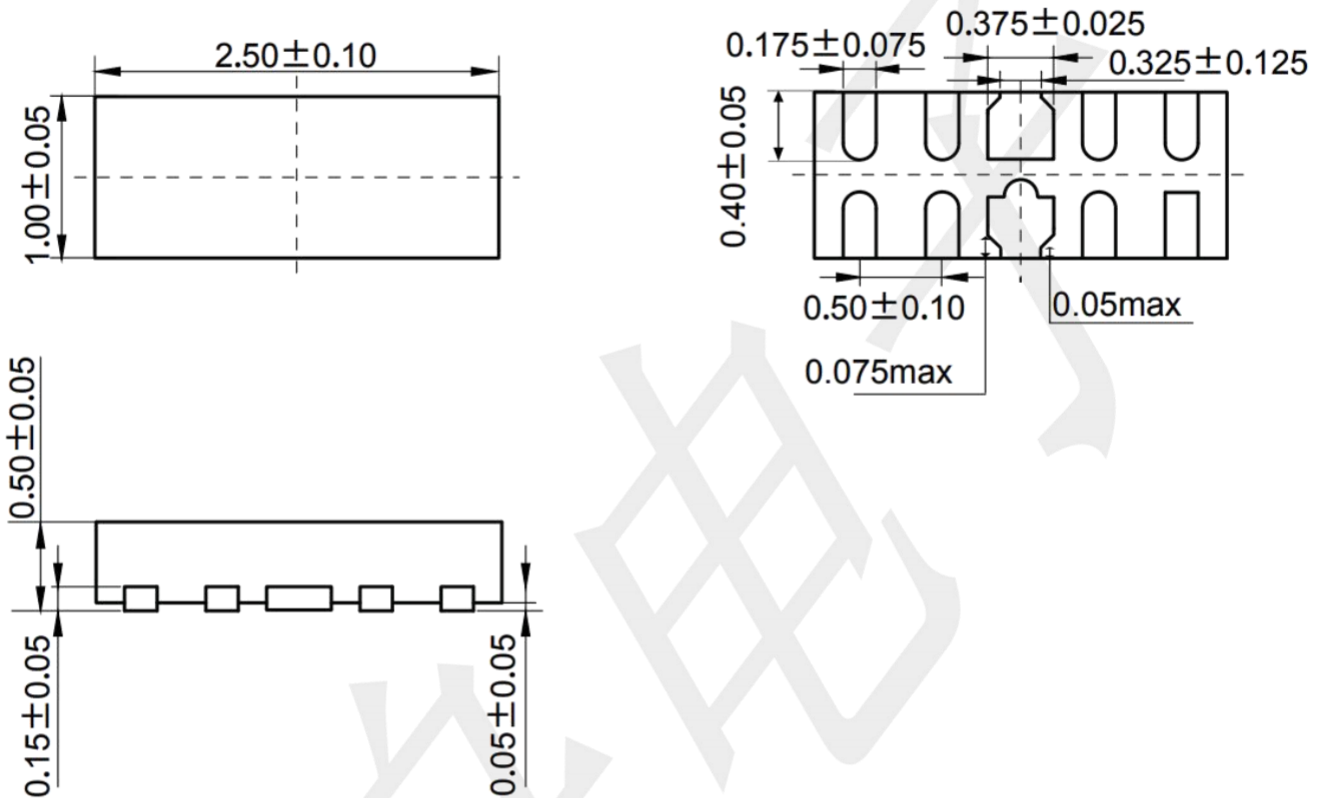


Fig3. Power Derating Curve



### Package Outline Dimensions (unit: mm)

#### DFN2510-10



### Mounting Pad Layout (unit: mm)

